

| Ref # | Hits | Search Query  | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|------|---|---|------------------|---------|------------------|
| S76   | 1    | (epitaxial near3 (GaN gallium near nitride)) with (silicon near nitride SiN) with chamber | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/05 18:41 |
| S77   | 181  | (epitaxial near3 (GaN gallium near nitride)) with buffer                                  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/06 18:29 |
| S78   | 501  | (epitaxial near3 (GaN gallium near nitride)) with nitride                                 | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/05 18:35 |
| S79   | 643  | (epitaxial near3 (GaN gallium near nitride)) with substrate                               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/05 18:35 |
| S80   | 857  | S76 or S77 or S78 or S79  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/05 18:36 |
| S81   | 586  | S76 or S77 or S78   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/05 18:36 |
| S82   | 147  | S81 and chamber   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/05 18:37 |
| S83   | 321  | S81 and silicon   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/05 18:37 |
| S84   | 154  | S83 and silicon near nitride  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/05 18:37 |

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| S85 | 154  | S84 and (GaN gallium near nitride) with epitaxial\$3               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 18:39 |
| S86 | 53   | S84 and (silicon near nitride) with epitaxial\$3                   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 18:39 |
| S87 | 126  | S81 and (GaN gallium near nitride) with (silicon near nitride SiN) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 18:41 |
| S88 | 1    | S87 and (GaN near nitride SiN) with chamber                        | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 18:42 |
| S89 | 0    | S87 and (GaN near nitride) with chamber                            | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 18:42 |
| S90 | 19   | S87 and (GaN gallium near nitride) with chamber                    | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 20:04 |
| S91 | 4    | pyrolitic near silicon adj nitride                                 | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 20:10 |
| S92 | 1128 | pyrolitic  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 20:09 |
| S93 | 7    | pyrolitic near5 silicon adj nitride                                | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 20:14 |
| S94 | 54   | pyrolitic near deposition  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 20:13 |

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| S95 | 0 | S94 with passivation         | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 20:12 |
| S96 | 2 | S94 with dielectric          | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 20:12 |
| S97 | 4 | S94 with silicon adj nitride | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/06 09:54 |
| S98 | 7 | "4586243"                    | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/05 20:19 |

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|-------|-------|--|---|------------------|---------|------------------|
| L7    | 11124 | ((metal near insulator near semiconductor near fird near effect near transistor) MISFET) ((high near electron near mobility near transistor) HEMT) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/06 17:19 |
| L8    | 255   | (source and drain and gate) near5 ((wet near2 etch\$3) (dry near2 etch\$3))  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/06 17:38 |
| L9    | 26    | 7 and 8  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/06 17:21 |
| L10   | 85    | (source and drain and gate) near5 (wet near2 etch\$3)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/06 18:52 |
| L11   | 2     | 7 and 10   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/06 17:54 |
| L12   | 0     | 11 and dry near2 etch\$3   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/06 17:54 |
| L16   | 0     | l10 and (epitaxial near3 (GaN gallium near nitride)) with buffer   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/06 18:31 |
| L17   | 4     | l10 and (light near emitting near device LED)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/06 18:31 |
| L18   | 9308  | (source and drain and gate) and (wet near2 etch\$3) and (dry near2 etch\$3)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/05/06 18:54 |

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| L19 | 704 | 7 and 18   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/06 18:53 |
| L20 | 235 | passivat\$3 near layer with (source<br>and drain and gate) and (wet<br>near2 etch\$3) and (dry near2<br>etch\$3) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/06 18:55 |
| L21 | 4   | 7 and 20   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/05/06 18:55 |